Title: DEVICE AND METHOD FOR
PRODUCING SINGLE CRYSTALS BY VAPOUR
DEPOSITION
Inventor: Erik JANZÉN et al.
Attorney Docket: 35947-202834

1/6

Figures

Figure 1

Title: DEVICE AND METHOD FOR
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DEPOSITION
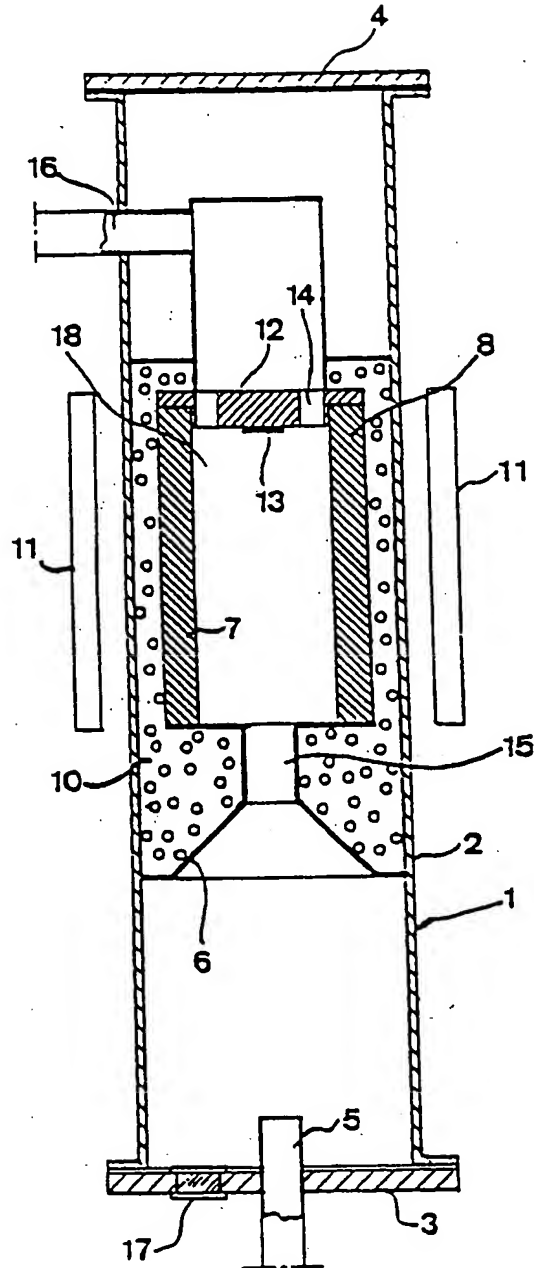Inventor: Erik JANZÉN et al.
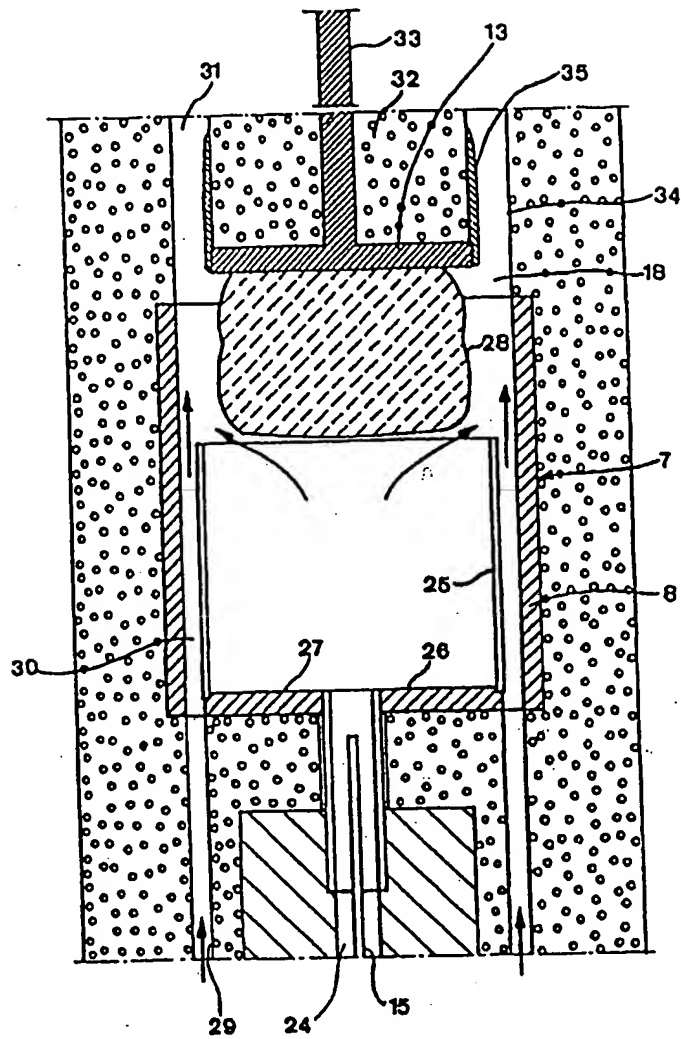Attorney Docket: 35947-202834

2/6

Figure 2

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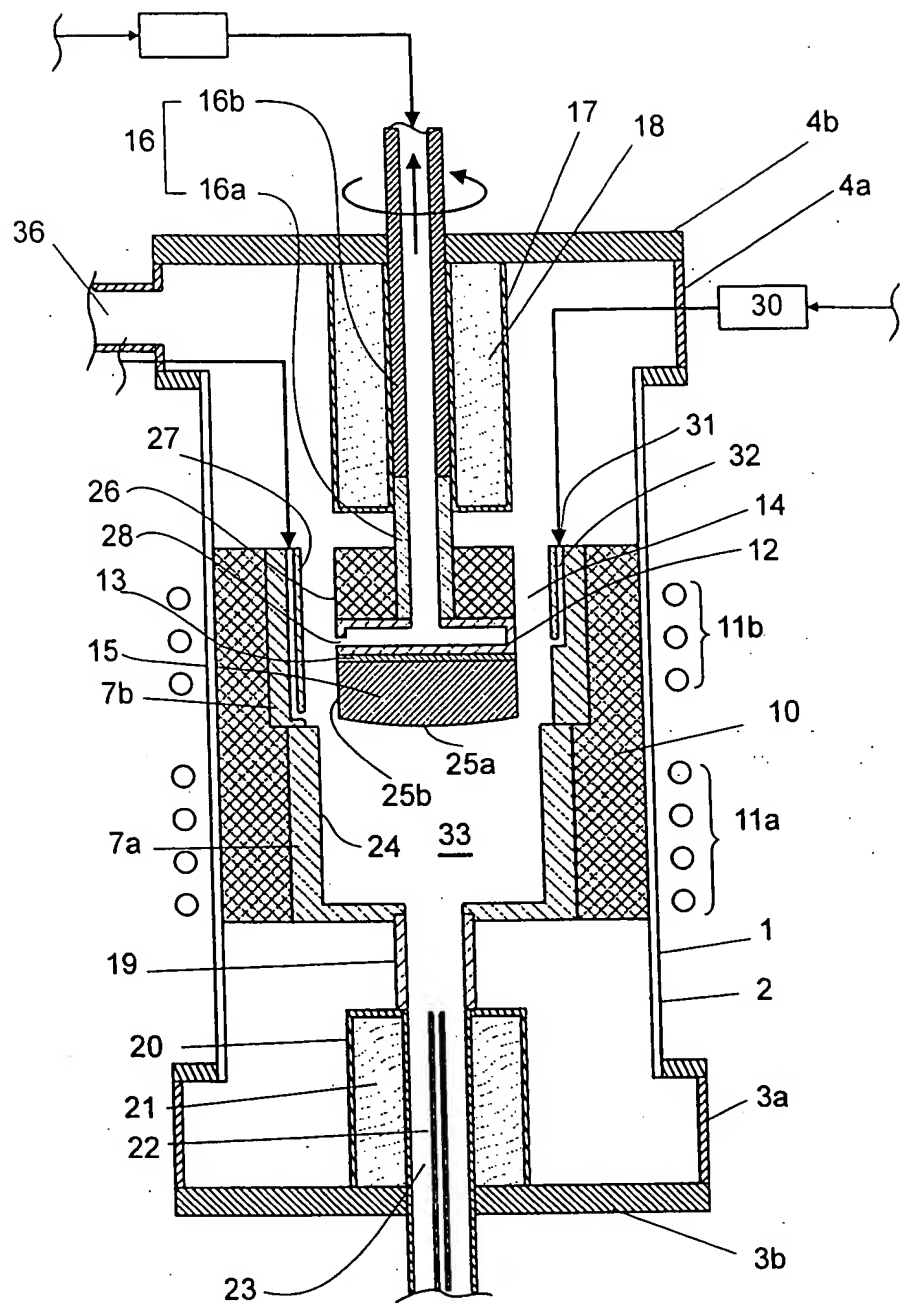Attorney Docket: 35947-202834

3/6

Figure 3

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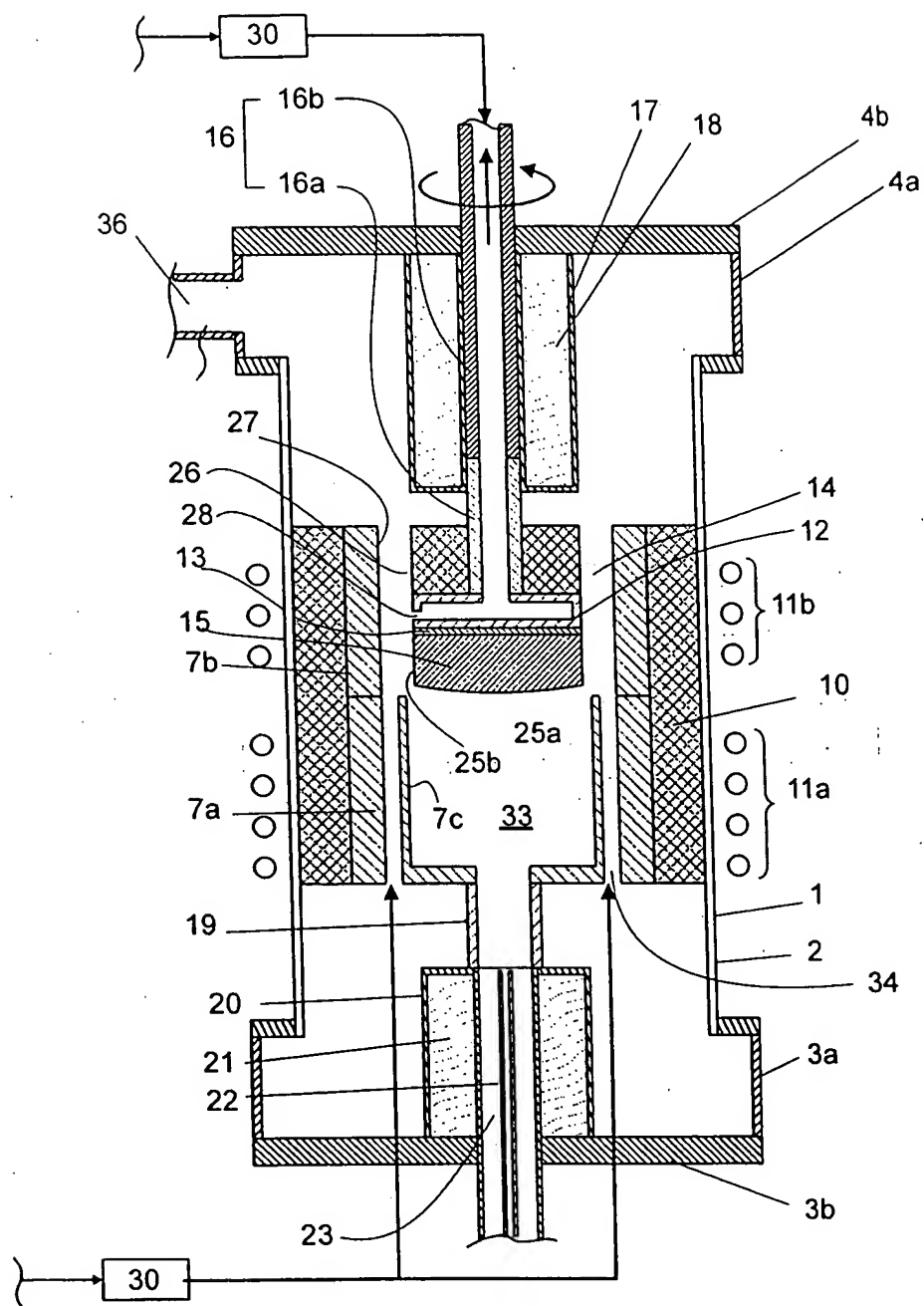Attorney Docket: 35947-202834
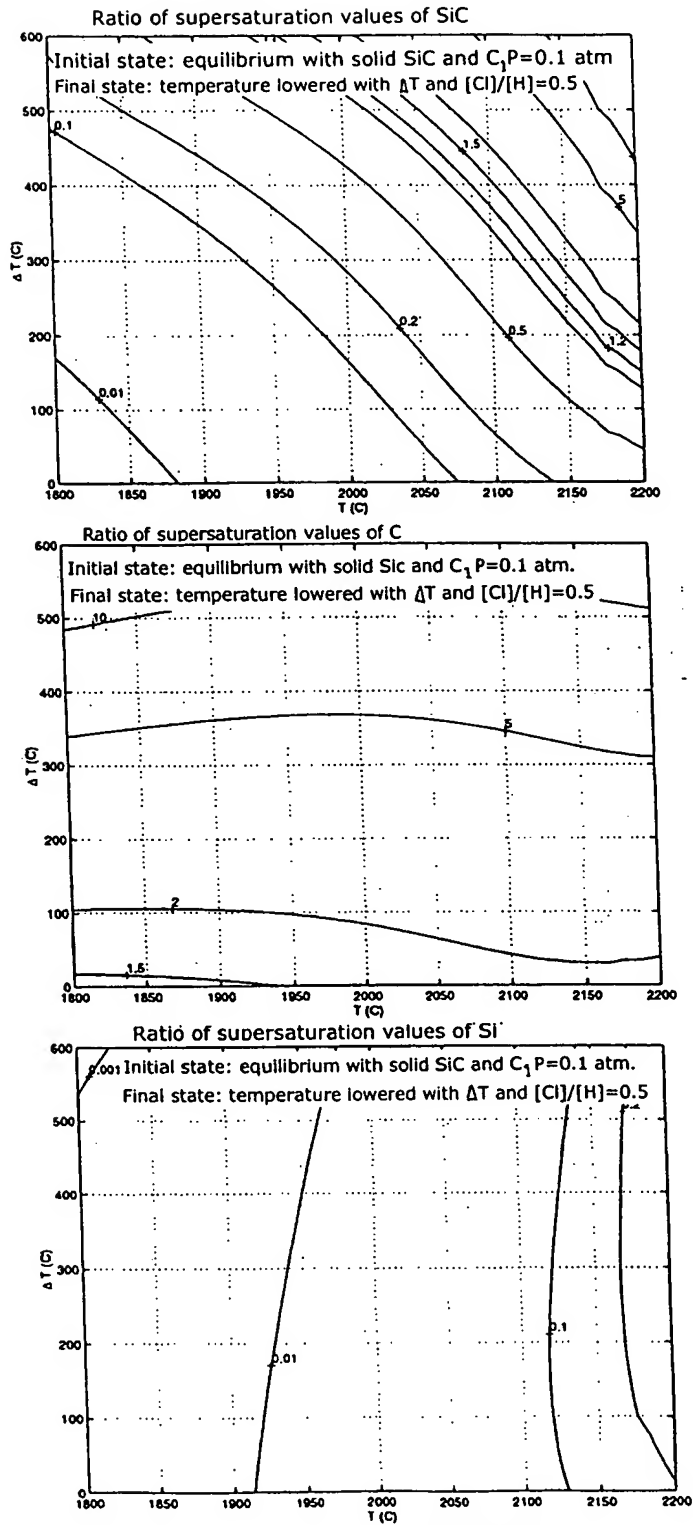
4/6

Figure 4

Figure 5

Ratio of supersaturation values of SiC

Intial state: equilibrium with solid SiC and $C_1 P = 0.12$ atm.
Final state: temperature lowered with ΔT and $[Cl]/[H]=1.2$

Ratio of supersaturation values of C

Initial state: equilibrium with solid SiC and $C_1 P=0.12$ atm.
Final state: temperature lowered with ΔT and $[Cl]/[H]=1.2$

Ratio of supersaturation values of Si

Initial state: equilibrium with solid SiC and $C_1 P=0.12$ atm.
Final state: temperature lowered with ΔT and $[Cl/H]=1.2$

Figure 6